

45V N-Ch Power MOSFET

V_{DS}		45	V
$R_{DS(on),typ}$	$V_{GS}=10V$	3.5	$m\Omega$
$R_{DS(on),typ}$	$V_{GS}=4.5V$	4.6	$m\Omega$
I_D (Silicon Limited)		101	A
I_D (Package Limited)		60	

Part Number	Package	Marking
HGN045NE4SL	DFN5x6	GN045NE4SL

Parameter	Symbol	Value
Continuous Drain Current (Silicon Limited)	$T_C=25$	64
Continuous Drain Current (Package Limited)	$T_C=25$	60
Drain to Source Voltage	V_{DS}	45
Gate to Source Voltage	V_{GS}	-
Pulsed Drain Current	I_{DM}	220 A
Avalanche Energy, Single Pulse	E_{AS}	$L=0.3mH, T_C=25$ 60 mJ
Power Dissipation	P_D	-
Operating and Storage Temperature	T_J, T_{stg}	-

Absolute Maximum Ratings

Parameter	Symbol	Max
Thermal Resistance Junction-Case	$R_{\theta JC}$	
Thermal Resistance Junction-Ambient		

Electrical Characteristics at $T_j=25$ (unless otherwise specified)
Static Characteristics

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	45	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1	1.8	2.2	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V, V_{DS}=45V, T_j=25$	-	-	1	μA
		$V_{GS}=0V, V_{DS}=45V, T_j=100$	-	-	100	
Gate to Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	3.5	4.5	$m\Omega$
		$V_{GS}=4.5V, I_D=20A$	-	4.6	7.0	$m\Omega$
Transconductance	g_{fs}	$V_{DS}=5V, I_D=20A$	-	40	-	S
Gate Resistance	R_G	$V_{GS}=0V, V_{DS}$ Open, $f=1MHz$	-	1.6	-	Ω

Dynamic Characteristics

Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=20V, f=1MHz$	-	2159	-	pF
Output Capacitance	C_{oss}		-	756	-	
Reverse Transfer Capacitance	C_{rss}		-	118	-	
Total Gate Charge (10V)	$Q_g(10V)$	$V_{DD}=20V, I_D=20A, V_{GS}=10V$	-	42	-	nC
Total Gate Charge (4.5V)	$Q_g(4.5V)$		-	22	-	
Gate to Source Charge	Q_{gs}		-	4	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	10	-	
Turn on Delay Time	$t_{d(on)}$	$V_{DD}=20V, I_D=20A, V_{GS}=10V, R_G=10\Omega,$	-	12	-	ns
Rise time	t_r		-	10	-	
Turn off Delay Time	$t_{d(off)}$		-	41	-	
Fall Time	t_f		-	16	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_F=20A$	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R=20V, I_F=20A, di_F/dt=200A/\mu s$	-	30	-	ns
Reverse Recovery Charge	Q_{rr}		-	30	-	nC

Fig 1. Typical Output Characteristics

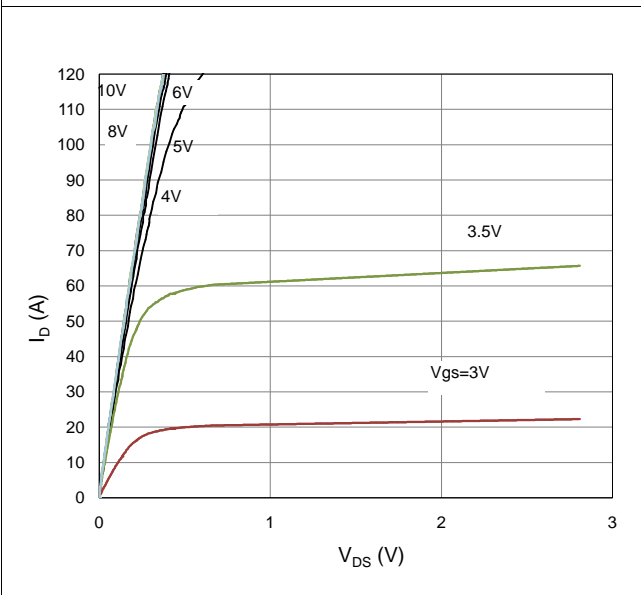


Figure 2. On-Resistance vs. Gate-Source Voltage

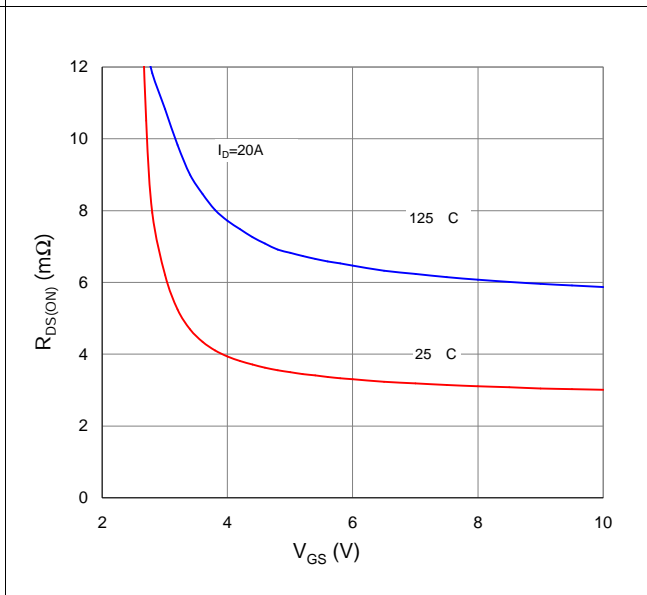


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

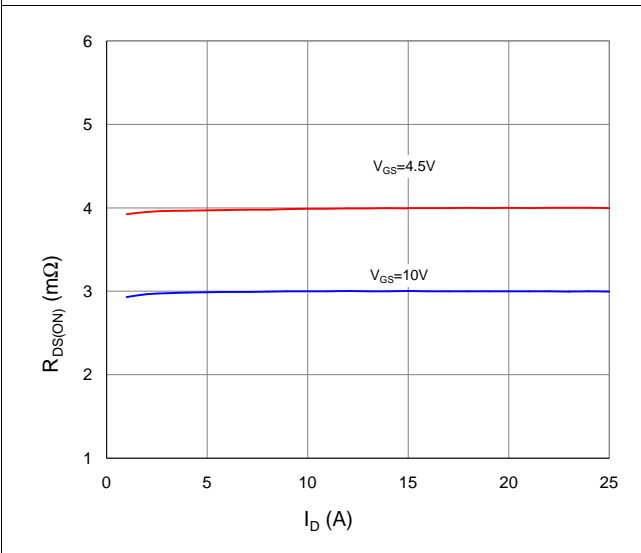


Figure 4. Normalized On-Resistance vs. Junction Temperature

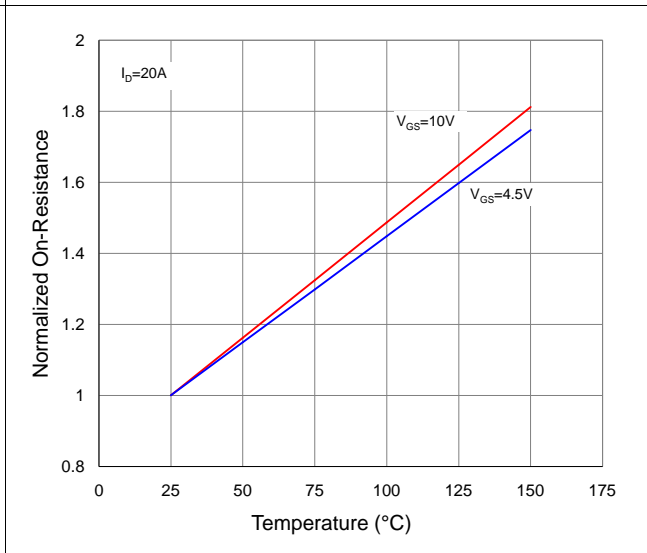


Figure 5. Typical Transfer Characteristics

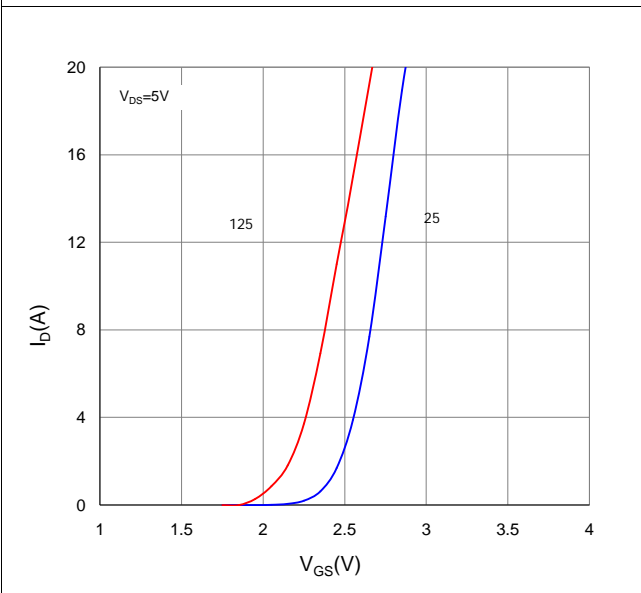


Figure 6. Typical Source-Drain Diode Forward Voltage

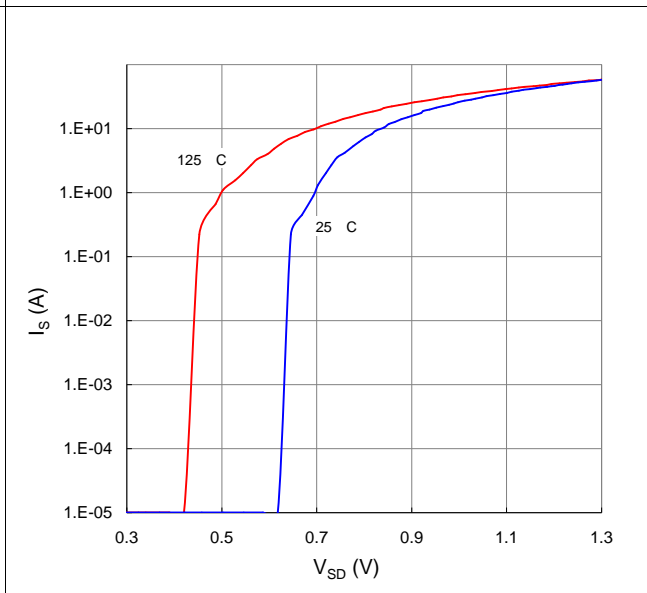


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

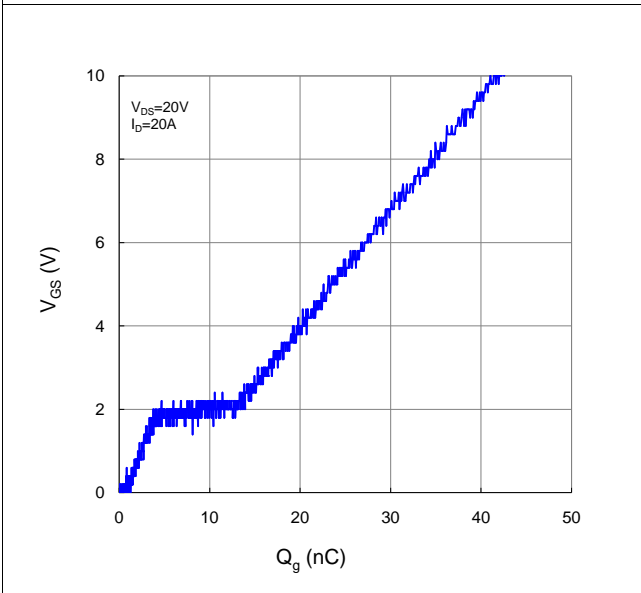


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

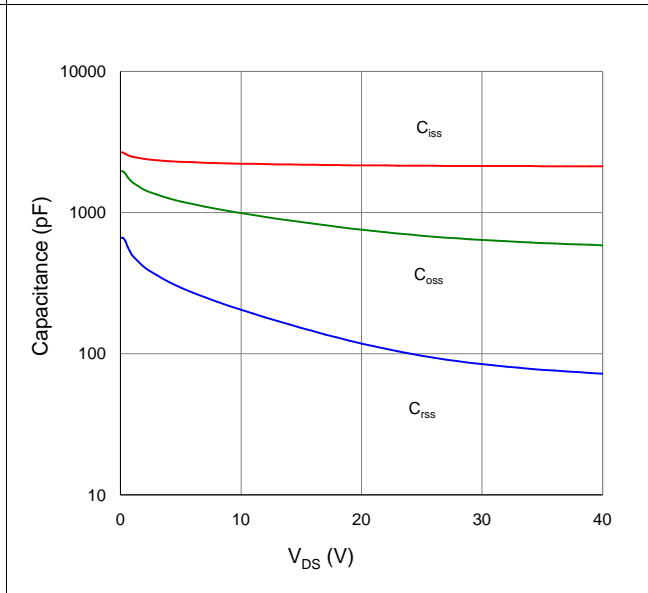


Figure 9. Maximum Safe Operating Area

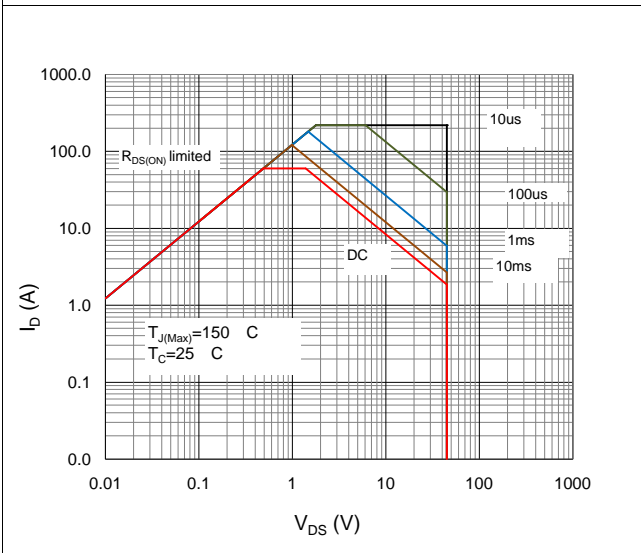


Figure 10. Maximum Drain Current vs. Case Temperature

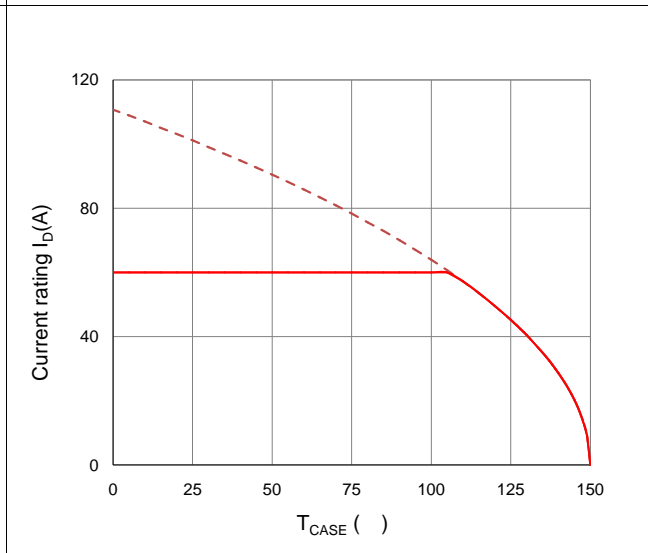
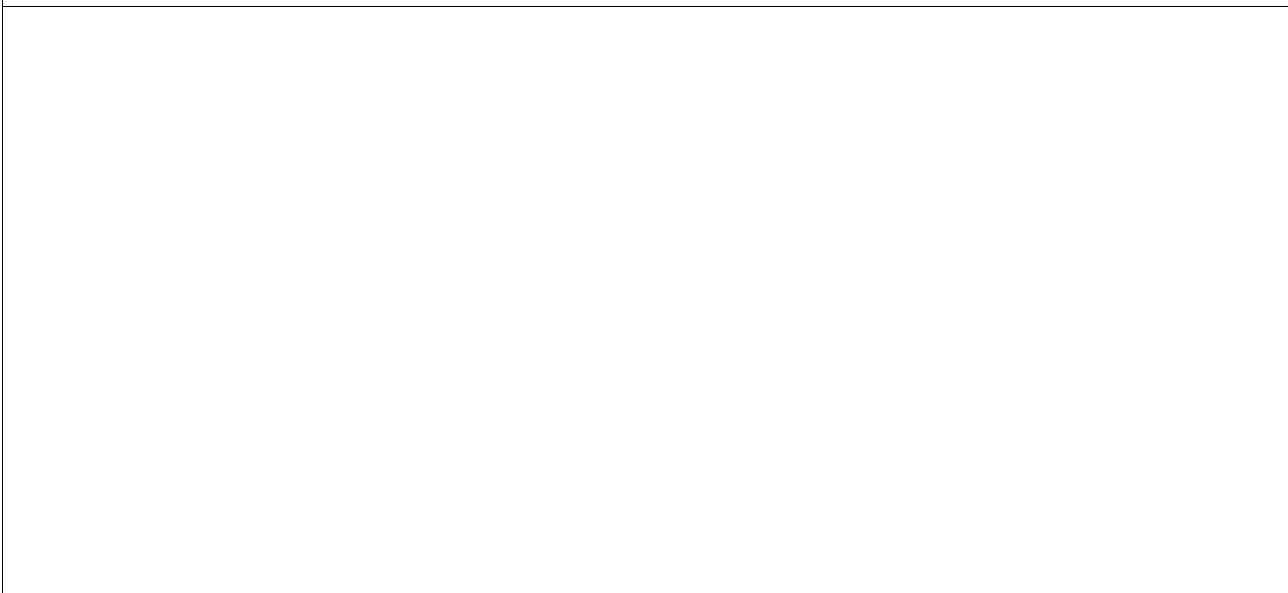


Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case



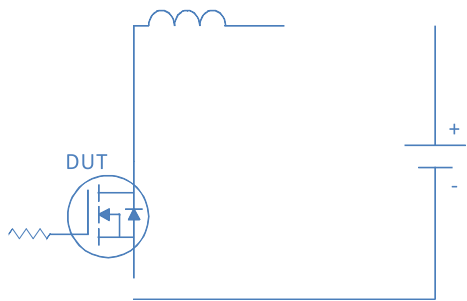
Inductive switching Test

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Gate Charge Test

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Uclamped Inductive Switching (UIS) Test

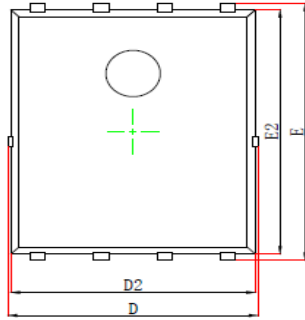


Diode Recovery Test

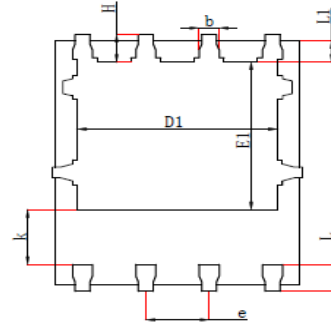
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Package Outline

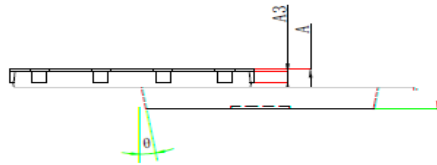
DFN5x6_P, 8 Leads



Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]